

Figure 3: A fix for the body effect problem.

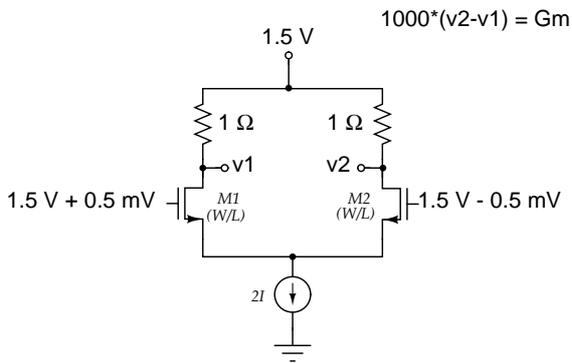


Figure 4: Measuring transconductance of M1.

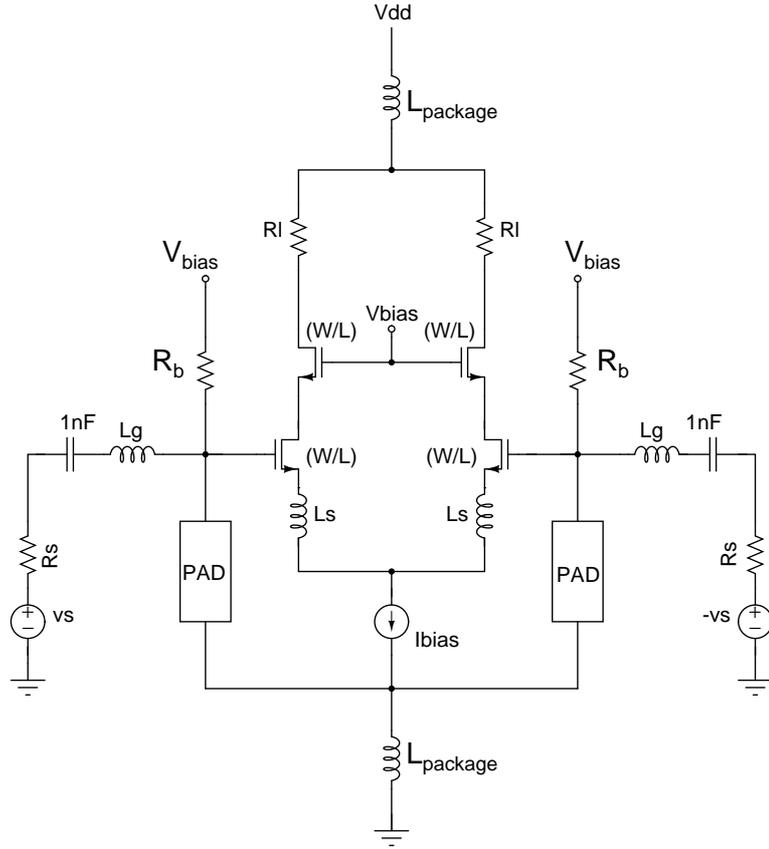


Figure 5: Fully differential LNA.

- First, analyze the circuit of Figure 2 (a). Assume that the bodies of all devices are tied to their sources and neglect output impedance of the devices. V_{dd} is 3.3 V. Find the current I and the transconductance of $Mb1$.
- Simulate the circuit in SPICE. Choose minimum length for all NMOS devices. V_{dd} is 3.3 V. Choose R to be $1\text{ k}\Omega$, and the gate overdrive of $Mb1$ to be $V_{gs} - V_t = 250\text{ mV}$. Plot the G_m of $M1$ as temperature is varied from $0 - 70^\circ\text{C}$. Next, keep temperature fixed at 300K and vary V_{dd} from $2.5-3.5\text{ V}$. What is the variation in transconductance?
- A fix for the body effect problem is shown in Figure 3. Analyze this circuit and redo (b) for this circuit. What do you notice?

- $|S_{11}|$ should be less than -12 dB .
- Voltage gain (ratio of differential output to differential input source voltage) of 16 dB .

Determine the IIP3 of your LNA.

4 DIFFERENTIAL LNA DESIGN

A differential LNA with the circuit topology shown in Figure 5 is to be designed. Assume $R_L = 250\ \Omega$. L_{package} represents the bondwire inductances of the package, and each has a value of 3 nH . The pads have a capacitance of 25 fF each. Each input port of the LNA should be matched to $50\ \Omega$. The supply voltage is 3.3 V . The maximum tail current I_{bias} allowable is 2.5 mA . The LNA should be functional and must meet the following performance specifications over the entire commercial temperature range of $0-70$ degree centigrade and a $\pm 10\%$ change in supply voltage. Design the appropriate biasing circuitry.